

● General Description

The AGM3416E combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

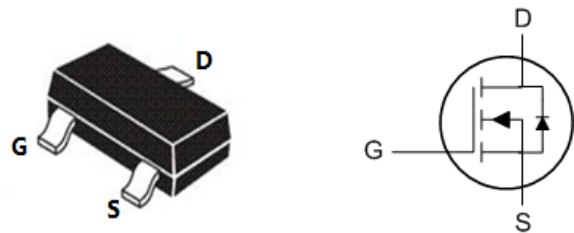
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
19.5V	10mΩ	6.5A

SOT-23-3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3416E	AGM3416E	SOT-23-3	178mm	8mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	19.5	V
VGS	Gate-Source Voltage (VDS=0V)	±10	V
ID	Drain Current-Continuous(TA=25°C) (Note 1)	6.5	A
	Drain Current-Continuous(TA=100°C)	3.9	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	26	A
PD	Maximum Power Dissipation(TA=25°C)	1.2	w
	Maximum Power Dissipation(TA=100°C)	0.48	w
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	105	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

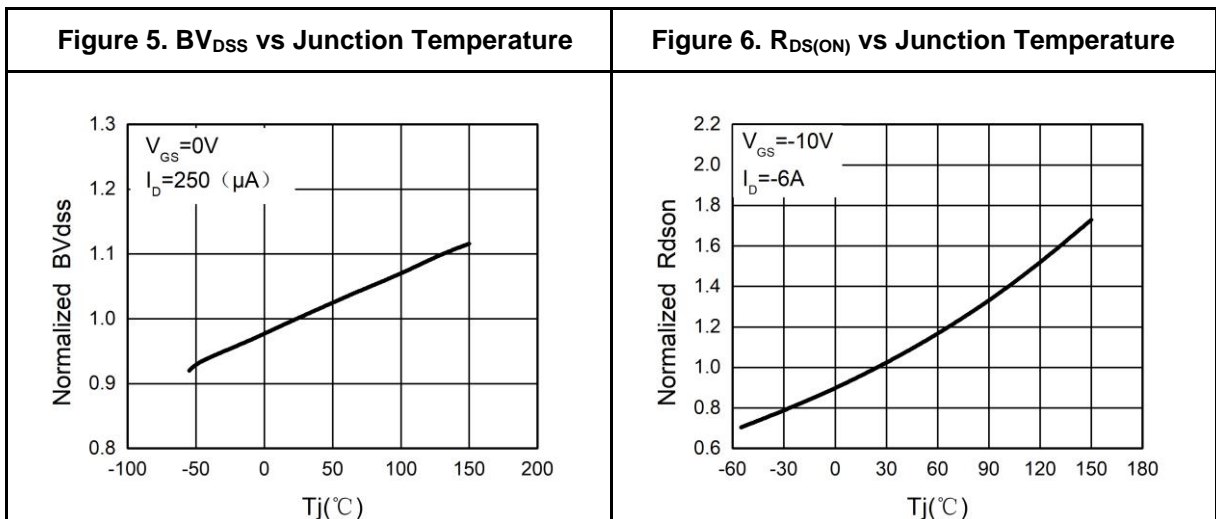
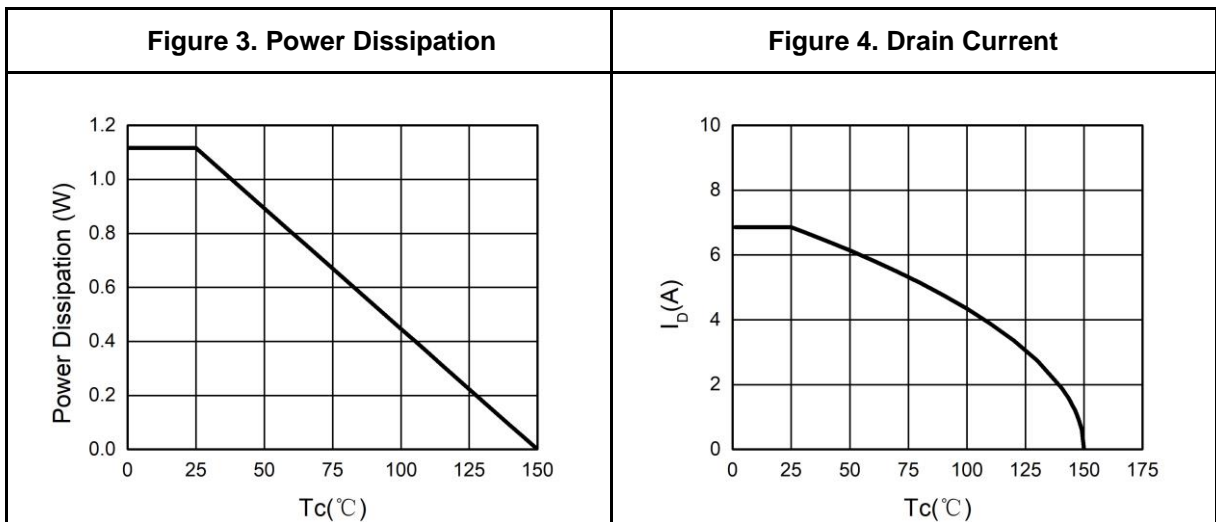
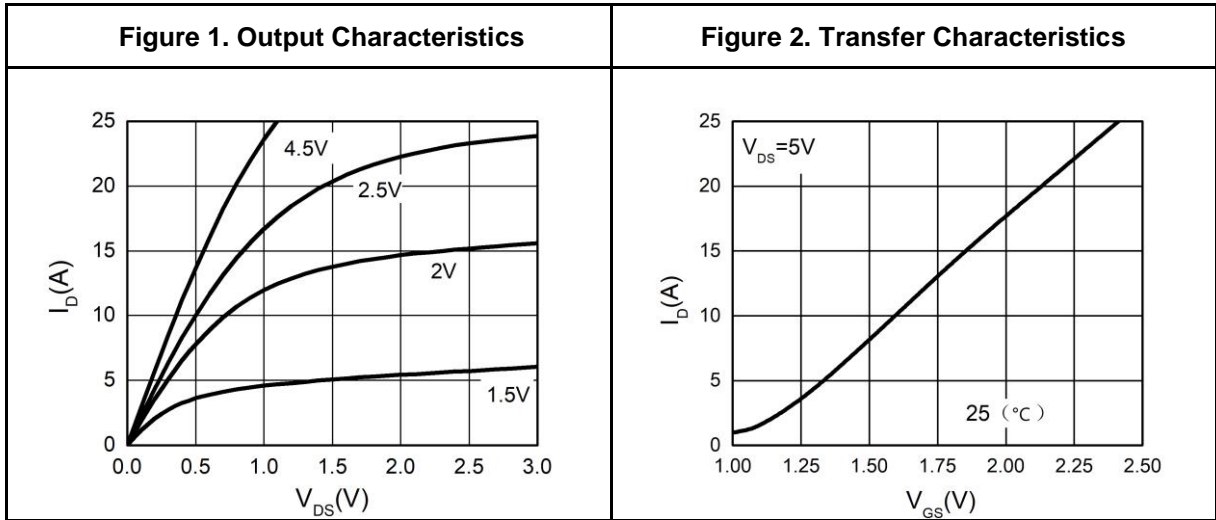
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	19.5	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=19.5V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±10V, VDS=0V	--	--	±10	μA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	0.5	0.7	1.0	V
gFS	Forward Transconductance	VDS=5V, ID=4A	--	5	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=4.5V, ID=5A	--	10	14	mΩ
		VGS=2.5V, ID=4A	--	12	18	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=10V, VGS=0V, F=1MHZ	--	854	--	pF
Coss	Output Capacitance		--	150	--	pF
Crss	Reverse Transfer Capacitance		--	90	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=5V, VDS=10V, RL=1.5Ω, RGEN=3Ω	--	11	--	nS
tr	Turn-on Rise Time		--	34	--	nS
td(off)	Turn-Off Delay Time		--	55	--	nS
tf	Turn-Off Fall Time		--	51	--	nS
Qg	Total Gate Charge	VGS=4.5V, VDS=10V, ID=6.5A	--	9.1	--	nC
Qgs	Gate-Source Charge		--	1.6	--	nC
Qgd	Gate-Drain Charge		--	2.0	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	6.5	A
VSD	Forward on Voltage	VGS=0V, IS=5A	--	--	1.2	V
trr	Reverse Recovery Time	IF=5A , dI/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

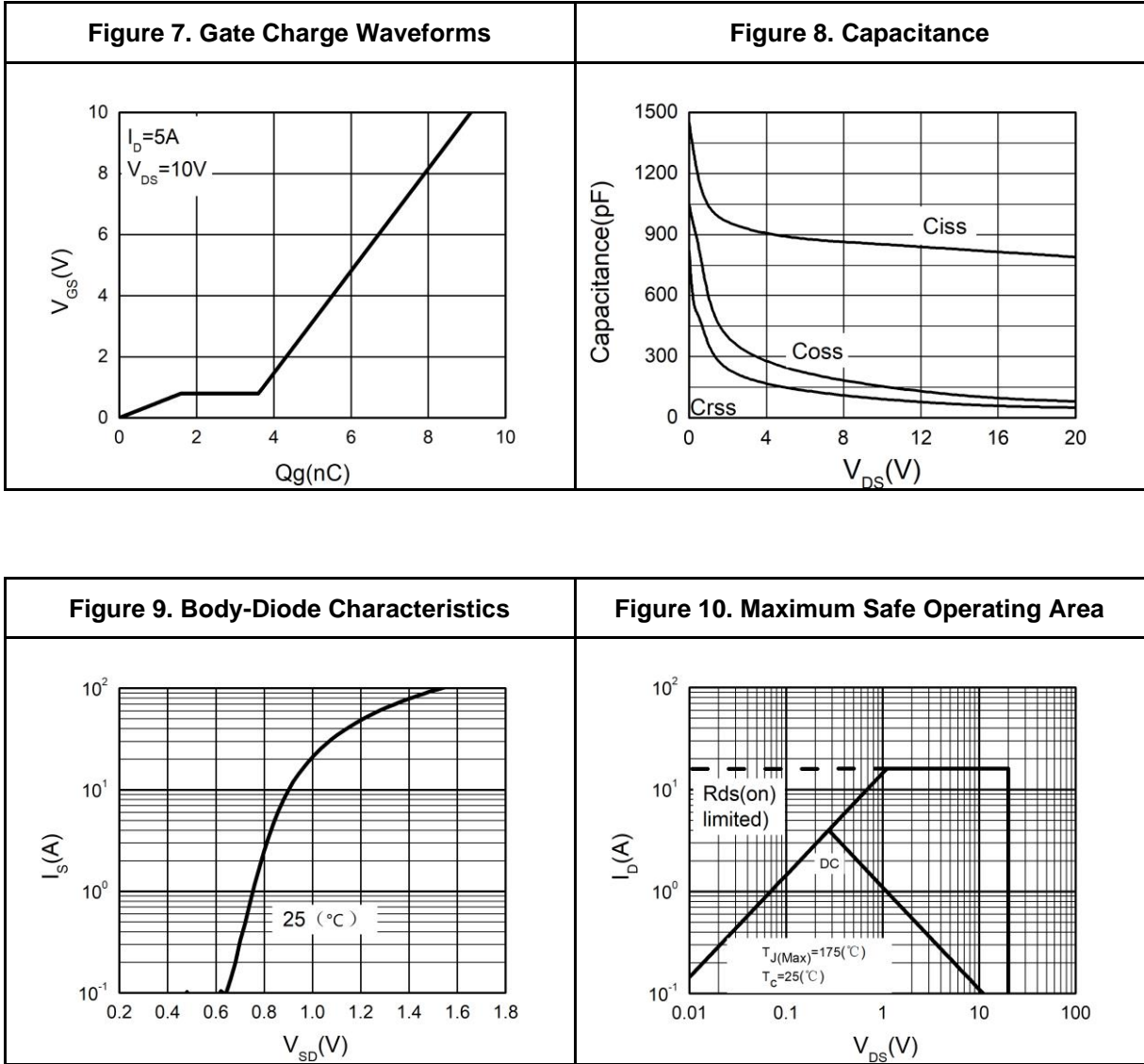
Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

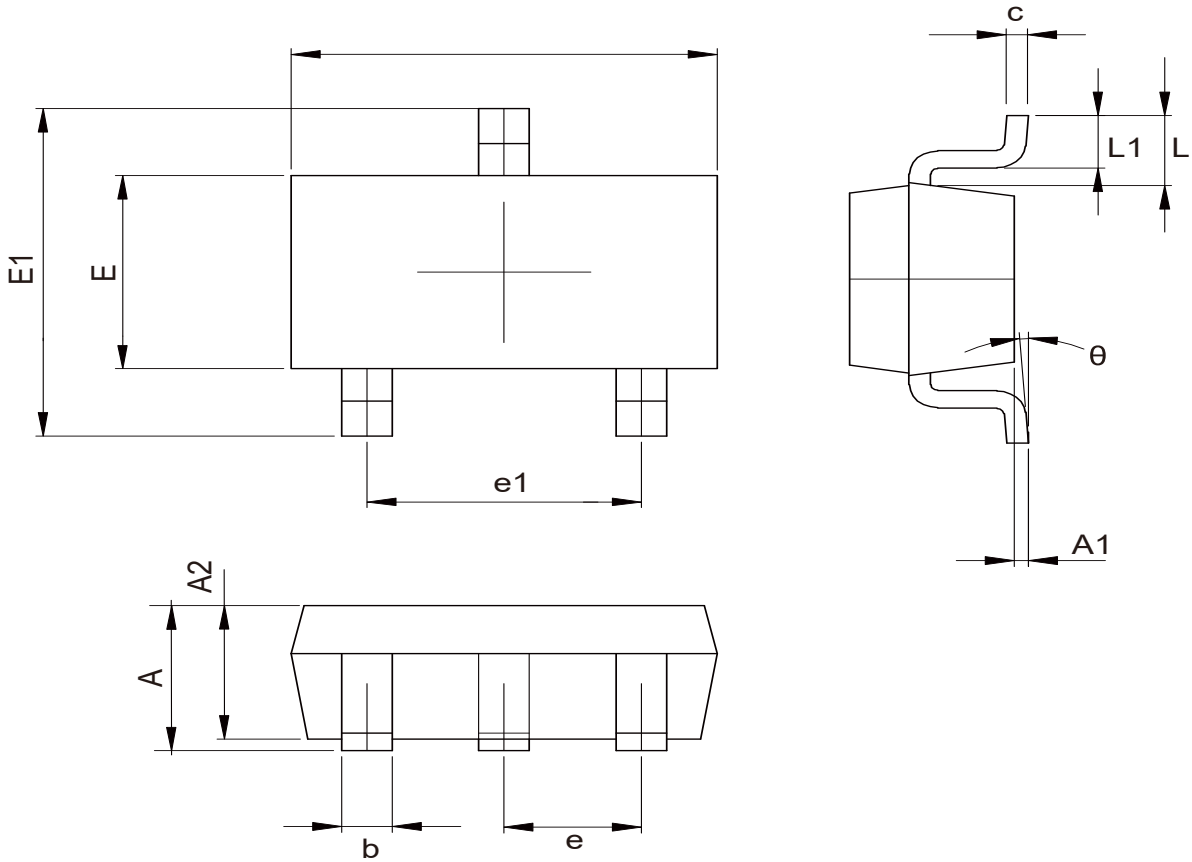
Typical Electrical And Thermal Characteristics (Curves)



Typical Electrical And Thermal Characteristics (Curves)



SOT-23-3L
PACKAGE OUTLINE DIMENSIONS



COMMON DIMENSIONS			
CUNITS MEASURE=MILLIMETER			
SYMBOL			
A	1.050	---	1.300
A1	0.000	---	0.200
b	0.300	0.400	0.500
c	0.100	---	0.200
D	2.820	2.900	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.6REF		
L1	0.300	0.450	0.600
θ	0°	--	8°

Unit:mm


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